



CeO₂ nanocrystals and solid-phase heteroepitaxy of CeAlO₃ interlayer on Al₂O₃(0001) substrate



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ARTICLE INFO

Article history:

Received 20 September 2016

Received in revised form 26 December 2016

Accepted 31 January 2017

Available online 3 February 2017

Communicated by Satoshi Uda

Keywords:

A1. Interface

A2. Hydrothermal crystal growth

A3. Solid phase epitaxy

B1. Nanomaterials

B1. Rare earth compounds

B1. Sapphire

ABSTRACT

Grain growth and interfacial solid state of CeO₂ nanocrystals (NCs) layer on Al₂O₃(0001) substrate were examined. CeO₂ NCs layer on Al₂O₃(0001) was prepared by dipping method using CeO₂ nanocrystals colloid solution. After heat treatment at 1000 °C in air, CeO₂ NCs layer was formed on Al₂O₃(0001). The CeO₂ NCs sintered to form a surface layer with an interlayer of CeAlO₃ after heat treatment at 950 °C in H₂/Ar, leading to dense and smooth CeO₂ NCs layer on Al₂O₃(0001) substrate. CeAlO₃ was grown via diffusion of CeO_{2-x} (non-stoichiometric CeO₂) and Al₂O₃, suggesting solid-phase reaction heteroepitaxy mechanism on Al₂O₃(0001) single crystal substrate.

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1. Introduction

Cerium dioxide (CeO₂, ceria) is one of the most important materials in the current industrial field due to its versatile properties for applications such as three-way catalysts for automobile, ultraviolet shielding materials, glass polishing agents, and electrolyte materials of solid oxide fuel cells [1–5]. CeO₂ films are attractive for various electronic and optical applications, silicon-on-insulator structures, miniaturized stable capacitors, oxygen sensors and optical coating [6–11]. Also, it is a promising candidate as buffer layer to prevent the chemical reaction between superconducting metal oxides such as YBa₂Cu₃O_{7-x} and Al₂O₃ substrate [12–16]. In general, CeO₂ film is prepared by dry process in vacuum including magnetron sputtering technique [17–19], pulsed laser deposition (PLD) [11,20,21] and molecular beam epitaxy (MBE) method [22,23]. We have reported a fabrication of CeO₂ NCs layer on Al₂O₃(0001) using CeO₂ nanocrystals (NCs) via simple dipping process [24]. However, the prepared CeO₂ NCs layer on Al₂O₃(0001) after heat treatment at 1000 °C for 3 h in air has voids among CeO₂ NCs and Al₂O₃(0001) substrate. In addition, in thin films fabrication, there is a problem about phenomenon that the sample thin film might crack at the interface between the prepared

thin film and the substrate after cooling, owing to the difference of the thermal expansion coefficients. Therefore, the strain from difference in the thermal expansion coefficient between the CeO₂ and Al₂O₃ should be considered when the CeO₂ films are applied to a buffer layer. In this work, we employed the process to prepare CeO₂ NCs layer on Al₂O₃(0001) single crystal substrate through the heat treatment in air, followed by heating under reductive condition, and investigated grain growth and interfacial solid state. The results showed that heat treatment in reducing condition using dilute hydrogen lead to dense and smooth CeO₂ NCs layer on Al₂O₃(0001) by sintering assisted with interlayer formation. An interlayer of CeAlO₃ was formed by solid-state reaction via diffusion of CeO_{2-x} (non-stoichiometric CeO₂) and Al₂O₃ resulting in growth orientation on substrate.

2. Experimental methods

2.1. Synthesis of CeO₂ nanocrystals

7 mmol of diammonium cerium(IV) nitrate ((NH₄)₂Ce(NO₃)₆, 95+, Wako Pure Chemical Industries) and 7 mmol of potassium oleate (C₁₇H₃₃COOK, 19% solution, Wako Pure Chemical Industries) were dissolved with 30 mL and 20 mL distilled water, respectively. The oleate solution was added into the cerium solution at room temperature under a vigorously stirred condition, followed by

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